

Title (en)

ETCHED-FACET RIDGE LASERS WITH ETCH-STOP

Title (de)

RIDGE-LASER MIT GEÄTZTEN FACETTEN MIT ÄTZSTOPP

Title (fr)

LASERS A SAILLIE A FACETTE GRAVEE DOTES D'ARRET DE GRAVURE

Publication

EP 2102950 A4 20170531 (EN)

Application

EP 06848109 A 20061226

Priority

US 2006049182 W 20061226

Abstract (en)

[origin: WO2008079120A1] A photonic device incorporate an epitaxial structure having an active region, and which includes a wet etch stop layer above, but close to, the active region. An etched-facet ridge laser is fabricated on the epitaxial structure by dry etching followed by wet etching. The dry etch is designed to stop before reaching the depth needed to form the ridge. The wet etch completes the formation of the ridge and stops at the wet etch stop layer.

IPC 8 full level

H01S 5/00 (2006.01)

CPC (source: EP)

H01S 5/0201 (2013.01); **H01S 5/0203** (2013.01); **H01S 5/028** (2013.01); **H01S 5/209** (2013.01)

Citation (search report)

- [X] WO 9411930 A1 19940526 - GTE LABORATORIES INC [US]
- [X] WO 03077390 A1 20030918 - OPTILLION AB [SE], et al
- [X] US 2002110341 A1 20020815 - YUANG RONG-HENG [TW]
- See references of WO 2008079120A1

Designated contracting state (EPC)

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DOCDB simple family (publication)

WO 2008079120 A1 20080703; CN 101569067 A 20091028; CN 101569067 B 20120425; EP 2102950 A1 20090923; EP 2102950 A4 20170531; JP 2010512659 A 20100422; JP 5264764 B2 20130814

DOCDB simple family (application)

US 2006049182 W 20061226; CN 200680056793 A 20061226; EP 06848109 A 20061226; JP 2009541287 A 20061226